



ACE17440M

N-Channel 40-V (D-S) MOSFET

Features

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

| PRODUCT SUMMARY | | |
|-----------------|----------------------------|-----------|
| V_{DS} (V) | $r_{DS(on)}$ (m Ω) | I_D (A) |
| 40 | 15 @ $V_{GS} = 10V$ | 15 |
| | 18 @ $V_{GS} = 4.5V$ | 14 |

Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Absolute Maximum Ratings

| Parameter | Symbol | Limit | Units |
|--|----------------|------------------|------------|
| Drain-Source Voltage | V_{DS} | 40 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current ^a | I_D | $T_A=25^\circ C$ | 15 |
| | | $T_A=70^\circ C$ | 12 |
| Pulse Drain Current ^b | I_{DM} | 50 | A |
| Continuous Drain Current (Diode Continuous) ^a | I_S | 6.4 | A |
| Power Dissipation ^a | P_D | $T_A=25^\circ C$ | 5 |
| | | $T_A=70^\circ C$ | 3.2 |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

| Parameter | Symbol | Maximum | Units |
|--|-----------------|-----------------------|-------|
| Maximum Junction-to-Ambient ^a | $R_{\theta JA}$ | $t \leq 10\text{sec}$ | 25 |
| | | Steady State | 65 |

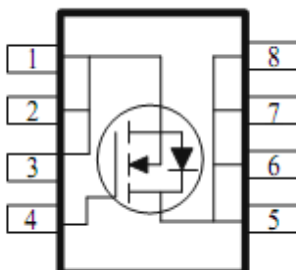
Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

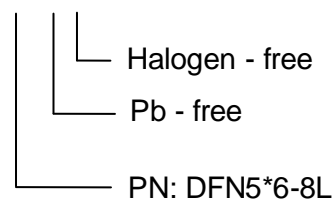
Packaging Type

DFN5*6-8L



Ordering information

ACE17440M XX + H





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Electrical Characteristics

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|--|--------------|---|------|------|-----------|------------|
| Static | | | | | | |
| Gate Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1 | | | V |
| Gate Body Leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=32V, V_{GS}=0V$ | | | 1 | uA |
| | | $V_{DS}=32V, V_{GS}=0V, T_J=55^\circ C$ | | | 25 | |
| On-State Drain-Current ^a | $I_{D(on)}$ | $V_{DS}=5V, V_{GS}=10V$ | 25 | | | A |
| Static Drain-Source On-Resistance ^a | $r_{DS(ON)}$ | $V_{GS}=10V, I_D=12A$ | | | 15 | m Ω |
| | | $V_{GS}=4.5V, I_D=9.6A$ | | | 18 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS}=15V, I_D=12A$ | | 22 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S=3.2A, V_{GS}=0V$ | | 0.75 | | V |
| Dynamic ^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS}=20V, V_{GS}=4.5V,$ $I_D=12A$ | | 19 | | nC |
| Gate-Source Charge | Q_{gs} | | | 5.0 | | |
| Gate-Drain Charge | Q_{gd} | | | 9.1 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DS}=20V, R_L=1.7\Omega$ $I_D=12A, V_{GEN}=10V$ $R_{GEN}=6\Omega,$ | | 7 | | ns |
| Rise Time | t_f | | | 38 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 62 | | |
| Fall Time | t_f | | | 24 | | |
| Input Capacitance | C_{iss} | $V_{DS}=15V, V_{GS}=0V$ $f=1MHz$ | | 1826 | | pF |
| Output Capacitance | C_{oss} | | | 253 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 208 | | |

Note:

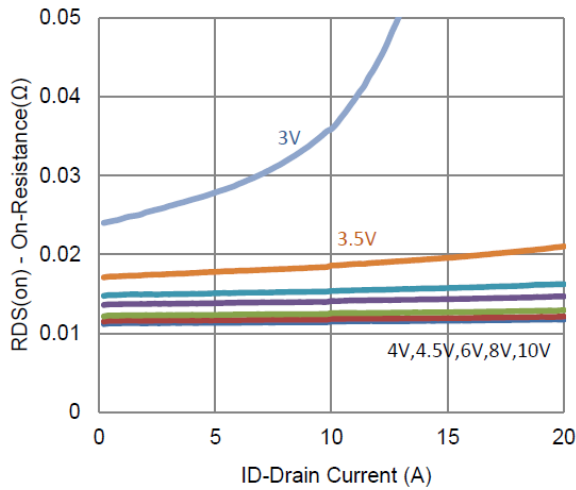
- a. Pulse test: PW \leq 300us duty cycle \leq 2%.
- b. Guaranteed by design, not subject to production testing.



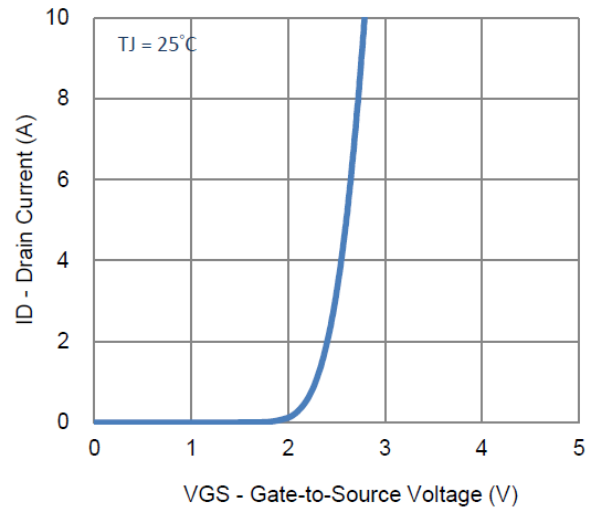
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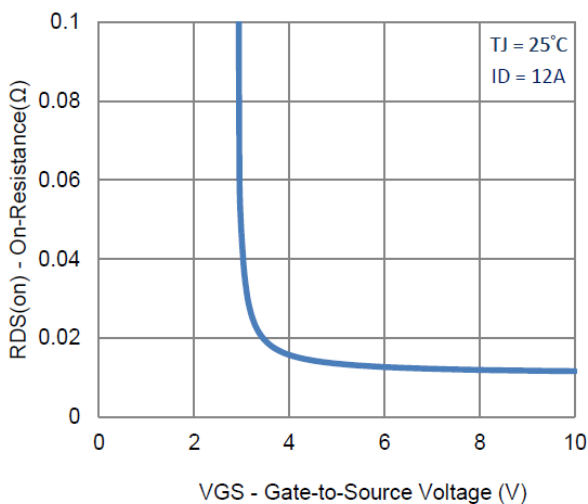
Typical Electrical Characteristics



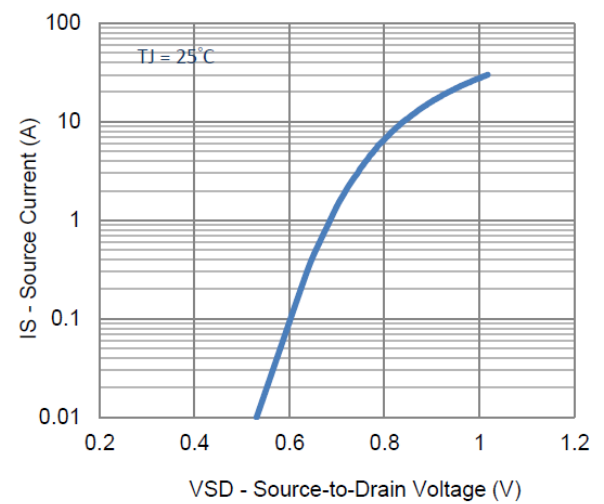
1. On-Resistance vs. Drain Current



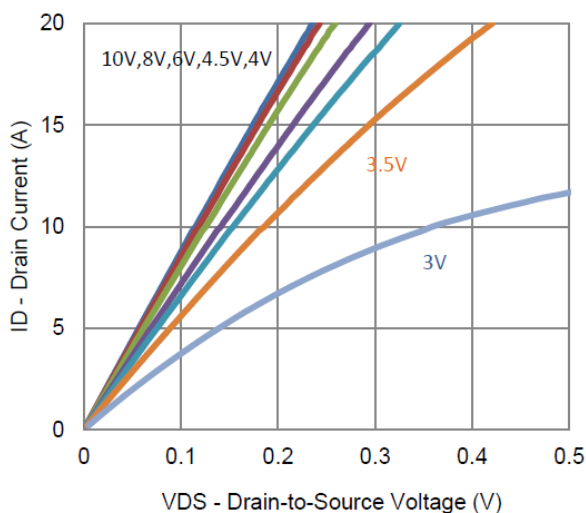
2. Transfer Characteristics



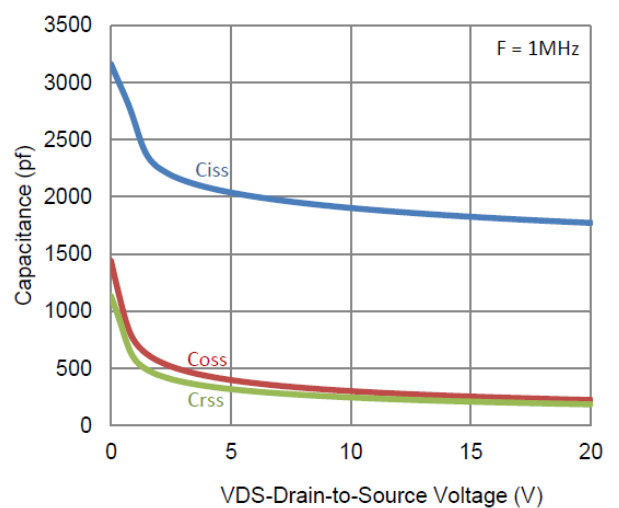
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics

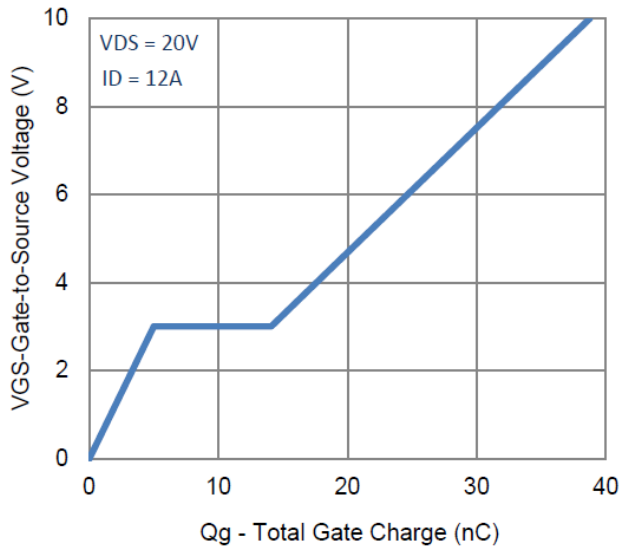


6. Capacitance

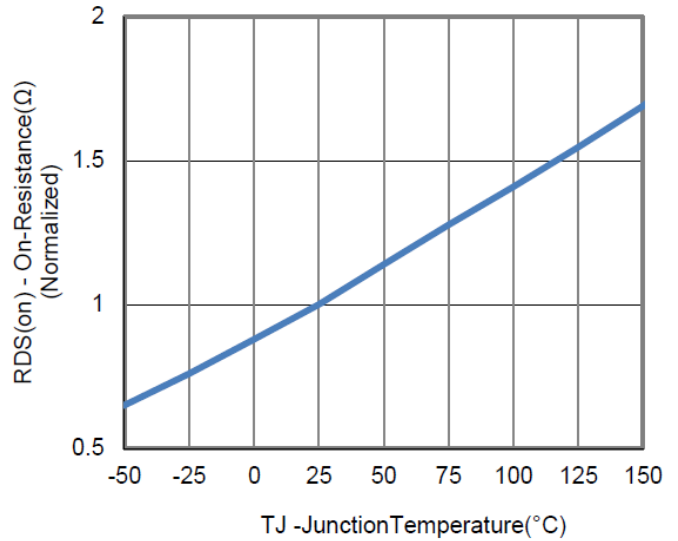


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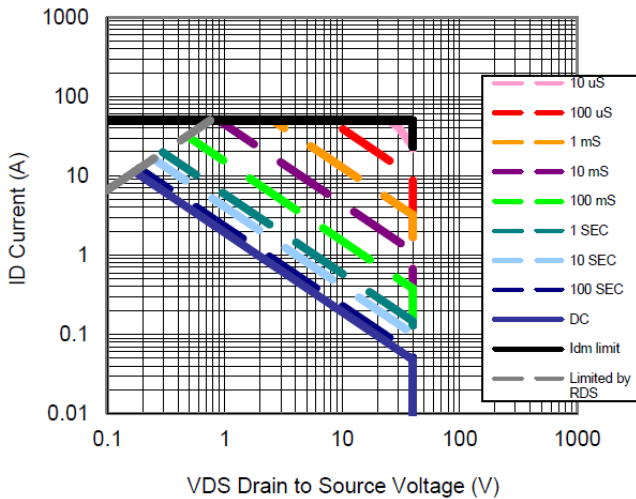
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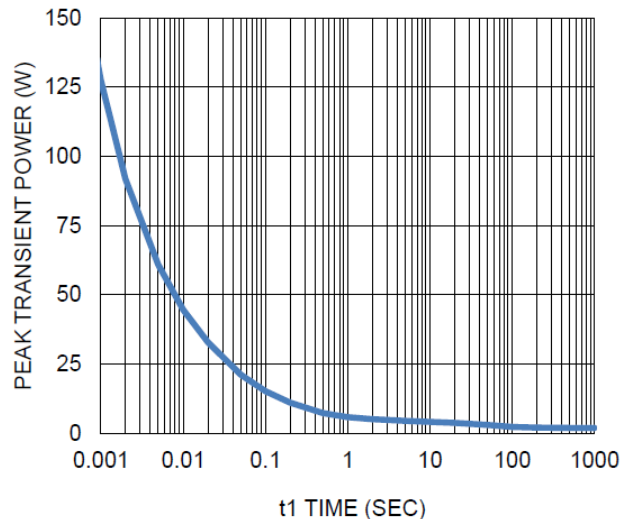
7. Gate Charge



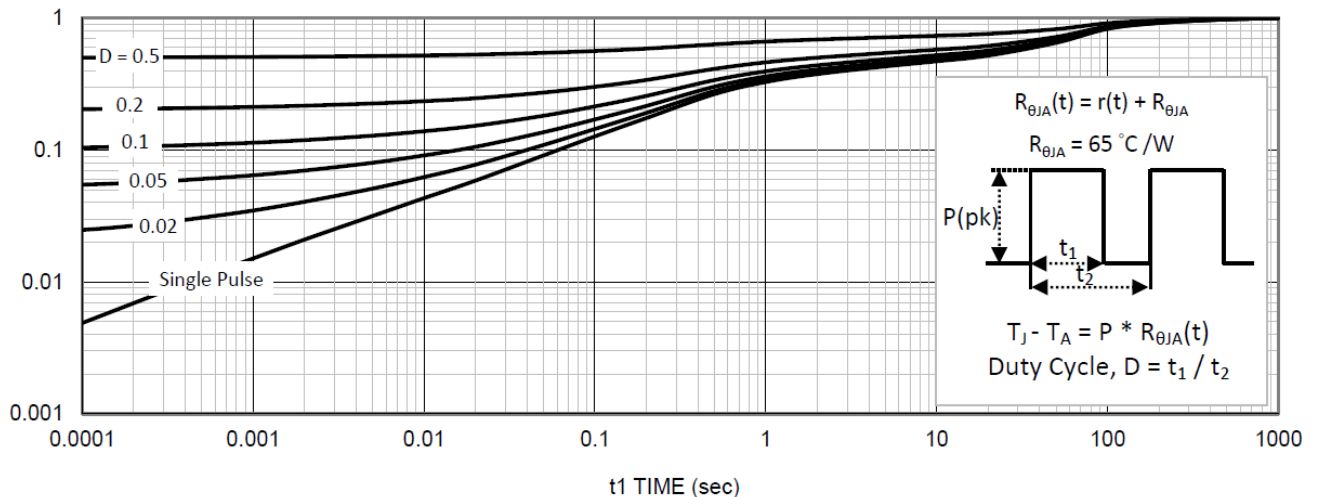
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

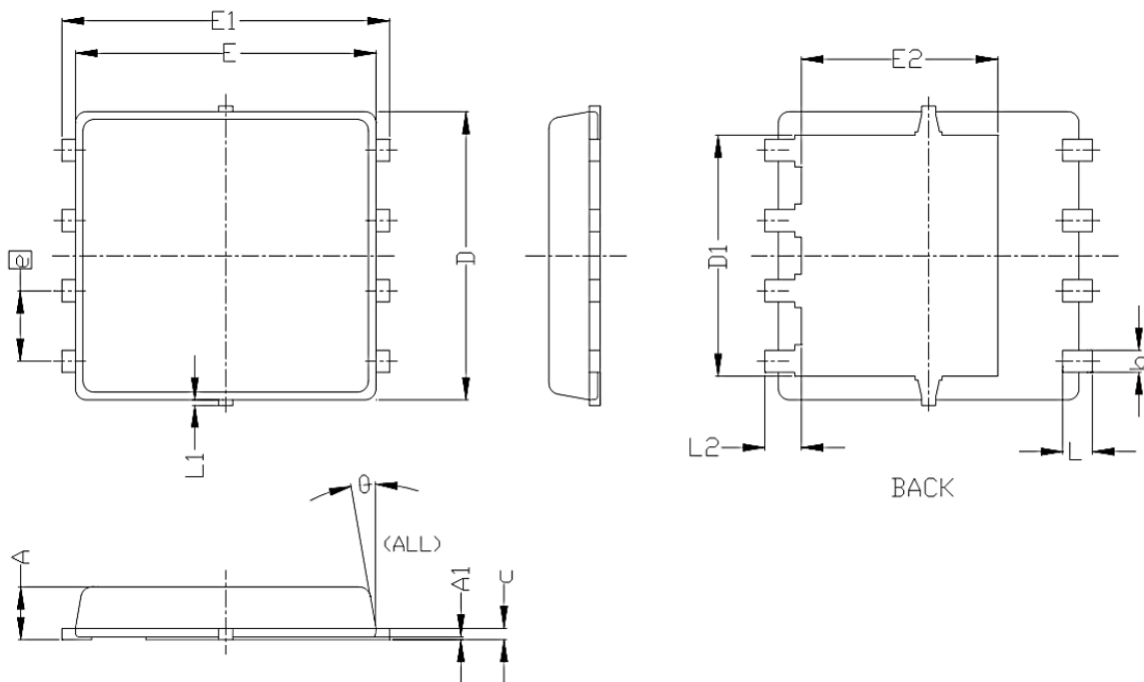


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Packing Information

DFN5*6-8L



| SYMBOLS | DIMENSIONS IN MILLIMETERS | | | DIMENSIONS IN INCHES | | |
|---------|---------------------------|------|------|----------------------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.85 | | | 0.033 | 0.037 | 0.039 |
| A1 | 0.00 | | | 0.000 | | 0.002 |
| b | 0.30 | | | 0.012 | 0.016 | 0.020 |
| c | 0.15 | | | 0.006 | 0.008 | 0.010 |
| D | 5.20BSC | | | 0.205BSC | | |
| D1 | 4.35BSC | | | 0.171BSC | | |
| E | 5.55BSC | | | 0.219BSC | | |
| E1 | 6.05BSC | | | 0.238BSC | | |
| E2 | 3.62BSC | | | 0.143BSC | | |
| e | 1.27BSC | | | 0.050BSC | | |
| L | 0.45 | 0.55 | 0.65 | 0.018 | 0.022 | 0.026 |
| L1 | 0 | | 0.15 | 0 | | 0.006 |
| L2 | 0.68REF | | | 0.027REF | | |
| theta1 | 0° | | 10° | 0° | | 10° |



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.